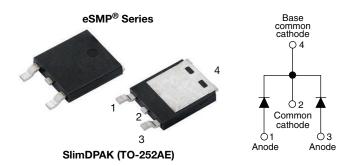
Vishay Semiconductors

Hyperfast Rectifier, 2 x 5 A FRED Pt[®]



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LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{F(AV)}	2 x 5 A				
V _R	200 V				
V _F at I _F	0.74 V				
t _{rr} (typ.)	16 ns				
T _J max.	175 °C				
Package	SlimDPAK (TO-252AE)				
Circuit configuration	Common cathode				

FEATURES

- Hyperfast recovery time
- 175 °C max. operating junction temperature
- Low forward voltage drop reduced Q_{rr} and soft recovery
- Low leakage current
- Very low profile typical height of 1.3 mm
- Ideal for automated placement
- Polyimide passivation for high reliability standard
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyper fast recovery rectifiers designed with optimized performance of forward voltage drop, hyper fast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: SlimDPAK (TO-252AE)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage		V _{RRM}		200	V		
Average rectified forward current	per leg		T _C = 165 °C	5	A		
Average rectilied for ward current	per device	I _{F(AV)}		10			
Non-repetitive peak surge current per leg		I _{FSM}	$T_J = 25 \ ^{\circ}C$, 10 ms sine pulse wave	100			
Operating junction and storage temp	peratures	T _J , T _{Stg}		-55 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	200	-	-		
Forward voltage		I _F = 5 A - 0.90	0.90	1.04			
	V _F	I _F = 10 A	-	1.0	1.17	V	
		I _F = 5 A, T _J = 150 °C	-	0.74	0.84		
		I _F = 10 A, T _J = 150 °C -	0.85	1.05			
Reverse leakage current per leg	I _R	V _R = V _R rated	-	-	4		
		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	80	μA	
Junction capacitance per leg	CT	V _R = 200 V	-	17	-	pF	

Revision: 18-Feb-2022

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Document Number: 96097

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST C	TEST CONDITIONS			MAX.	UNITS	
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t =$	-	16	-			
Reverse recovery time	+	I _F = 0.5 A, I _R = 1	A, I _{RR} = 0.25 A	-	-	25	ns	
neverse recovery time	t _{rr}	T _J = 25 °C		-	21	-	115	
		T _J = 125 °C	I _F = 5 A dI _F /dt = 200 A/μs V _B = 160 V	-	30	-		
Pools recovery oursent		T _J = 25 °C		-	2.5	-	А	
Peak recovery current	I _{RRM}	T _J = 125 °C		-	4	-	A	
	0	T _J = 25 °C]	-	25	-	nC	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	60	-	nc	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C	
Thermal resistance, junction to ambient	R _{thJA} ⁽¹⁾⁽²⁾		-	73	90	°C/W	
Thermal resistance, junction to mount, per diode	R _{thJM} ⁽³⁾		-	2.1	2.5	0/10	
Weight			-	0.20	-	g	
Marking device		Case style SlimDPAK (TO-252AE)		10C\	/H02		

Notes

- $^{(1)}$ The heat generated must be less than thermal conductivity from junction to ambient; $dP_D/dT_J < 1R_{thJA}$
- $^{(2)}$ Free air, mounted or recommended copper pad area; thermal resistance R_{thJA} junction to ambient
- ⁽³⁾ Mounted on infinite heatsink

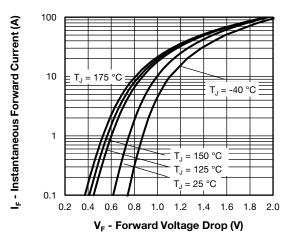


Fig. 1 - Typical Forward Voltage Drop Characteristics

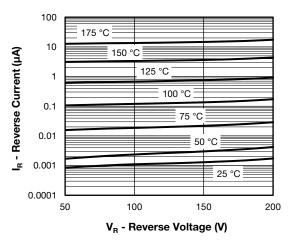


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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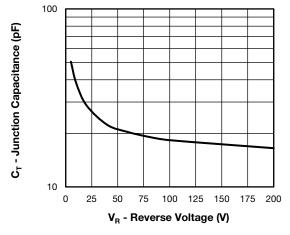


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

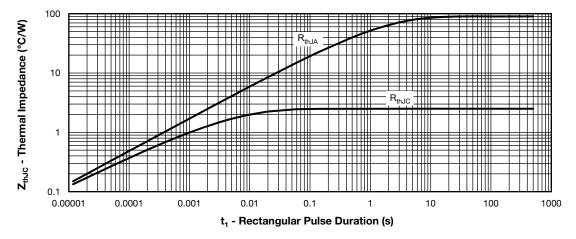
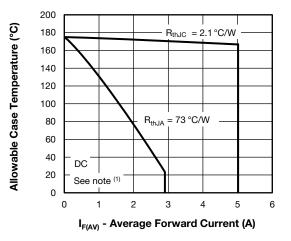
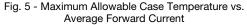


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

Average Power Loss (W)



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Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

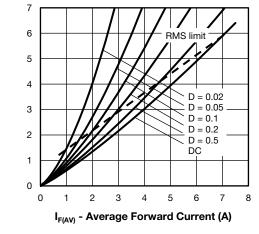


Fig. 6 - Forward Power Loss Characteristics

Revision: 18-Feb-2022

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Document Number: 96097

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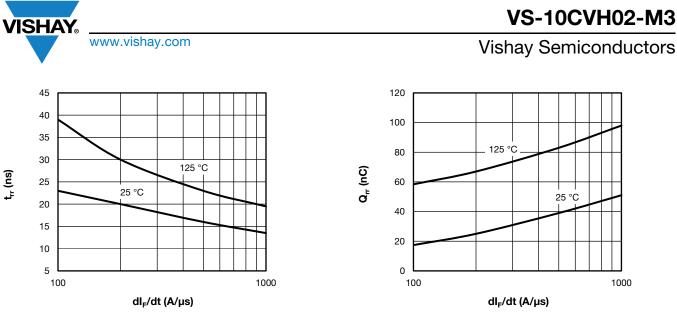


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

Fig. 8 - Typical Stored Charge vs. dl_F/dt

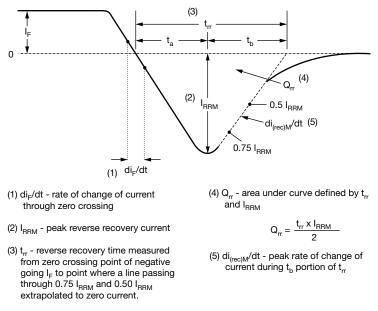


Fig. 9 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

Device code	vs-	10	<u> </u>	V	ш	02	MO
Device code	VS-	10	С	V	н	02	-M3
	1	2	3	4	5	6	7
	1	- Visł	nay Sen	niconduc	ctors pro	oduct	
	2	- Cur	rent rati	ng (10 =	= 10 A)		
	3	- Circ	uit conf	iguratior	า:		
		C =	commo	n catho	de		
	4	- V =	SlimDP	AK			
	5		Process type, H = hyper fast recovery				
	6	- Volt	tage coo	le (02 =	200 V)		
	7	M3	= halog	gen-free	, RoHS-	complia	ant, and

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-10CVH02-M3/I	4500	4500	13"diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96081				
Part marking information	www.vishay.com/doc?96085				
Packaging information	www.vishay.com/doc?88869				





SlimDPAK

DIMENSIONS in inches (millimeters)





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Revision: 01-Jul-2024